SSDM 2009 Time Table

Wednesday, October 7

2F Heisei

10:00-12:00 Opening / SSDM Award / Plenary Session 1

2F Heisei <Higashi>	2F Heisei <Naka>	2F Heisei <Nishi>	3F Sakura	4 F Hirose <Higashi>	4F Hirose <Nishi>	6F Kiri	6F Kaede	6F Hagi	6F Aoi
13:30-16:00 **Area 3:** A-1: SOI/GOI and Channel Engineering	**13:30-15:40** **Area 1:** B-1: Characterization	**13:30-15:40** **Area 5:** C-1: Interconnect-related Circuits Technology	**13:30-15:40** **Area 2:** D-1: 3D Integration	**13:30-15:45** **Area 10:** F-1: Organic Photonic Photovoltaic Device & Memory	**13:30-15:20** **Area 4:** G-1: DRAM	**13:30-15:45** **Area 8:** H-1: SiGe Related Technologies and III-V Nano Structures	**13:30-15:45** **Area 7:** I-1: Si Photonics and Photonic Crystals	**13:30-15:45** **Area 6:** J-1: GaN FETs and RF Devices	**13:30-15:45** **Area 9:** K-1: Single Electron and Quantum Transport
16:00-18:20 **Area 3:** A-2: Variability and RTS	**16:00-18:15** **Area 1:** B-2: Characterization and Process Technology	**16:00-18:00** **Area 5:** C-2: Power Management and Advanced Mixed-Signal Technology	**16:00-18:10** **Area 2:** D-2: RF Device/Process Technology	**16:00-18:00** **Area 10:** F-2: Organic Transistor	**16:00-17:50** **Area 4:** G-2: Flash Memory I	**16:00-18:15** **Area 8:** H-2: Graphen and Nanowires	**16:00-18:15** **Area 7:** I-2: Si Lightemitter and THz Laser	**16:00-18:15** **Area 6:** J-2: III-V High-mobility Channel Devices	**16:00-17:45** **Area 9:** K-2: Thinfilm Transistor and Memory

19:00-21:00 Banquet/Paper Award & Young Researcher Award (Heisei)

Thursday, October 8

2F Heisei <Higashi>	2F Heisei <Naka>	2F Heisei <Nishi>	3F Sakura	4 F Hirose <Higashi>	4F Hirose <Nishi>	6F Kiri	6F Kaede	6F Hagi	6F Aoi
8:45-10:30 **Short Presentation** Area 3 8:45 ～ 9:54, Area 12 10:00 ～ 10:24			**8:45-10:30** **Short Presentation** Area 4 8:45 ～ 9:27, Area 5 9:35 ～ 10:11	**8:45-10:30** **Short Presentation** Area 10 8:45 ～ 10:00	**8:45-10:30** **Short Presentation** Area 1 8:45 ～ 10:09	**8:45-10:30** **Short Presentation** Area 7 8:45 ～ 9:48, Area 14 9:55 ～ 10:28	**8:45-10:30** **Short Presentation** Area 2 8:45 ～ 9:30, Area 8 9:40 ～ 10:22	**8:45-10:30** **Short Presentation** Area 6 8:45 ～ 9:39, Area 13 9:45 ～ 10:27	**8:45-10:30** **Short Presentation** Area 9 8:45 ～ 9:39, Area 11 9:45 ～ 10:21

10:30-12:00 Poster Session 2F Heisei<Naka & Nishi>

13:05-14:40 **Area 1:** A-3: Source/Drain Engineering					**13:15-14:35** **Area 4:** G-3: Flash Memory II	**13:15-14:45** **Area 8:** H-3: Oxide Materials	**13:15-14:45** **Area 7:** I-3: LED I	**13:15-14:45** **Area 6:** J-3: SiC and Diamond Devices	**13:15-14:45** **Area 9:** K-3: Electron Spin and Quantum Information

2F Heisei <Higashi & Naka>

15:00-15:45 Plenary Session 2

2F Heisei <Higashi>	2F Heisei <Naka>	2F Heisei <Nishi>	3F Sakura	4 F Hirose <Higashi>	4F Hirose <Nishi>	6F Kiri	6F Kaede	6F Hagi	6F Aoi
16:30-17:10 **Area 3:** A-4: Novel Device Structure and Physics	**16:00-17:30** **Area 1:** B-4: High-k/Metal Gate I		**16:00-17:10** **Area 2:** D-4: Scaled-down Cu Metallization	**16:00-17:15** **Area 10:** F-4: Organic Transistor	**16:00-17:20** **Area 4:** G-4: Flash Memory III	**16:00-17:15** **Area 8:** H-4: Advanced Nitride Growth and Structures	**16:00-17:15** **Area 13:** I-4: Compound Semiconductor Nanowires	**16:00-17:15** **Area 6:** J-4: High-frequency Devices	**16:00-17:15** **Area 9:** K-4: Nanomechanical Systems
17:30-18:50 **Area 3:** A-5: New Device Technologies	**17:40-19:00** **Area 1:** B-5: High-k/Metal Gate II		**17:30-18:40** **Area 2:** D-5: Characterization and Reliability for Metallization	**17:30-18:30** **Area 10:** F-5: Organic Transistor	**17:30-18:20** **Area 4:** G-5: PRAM	**17:30-18:45** **Area 8:** H-5: Advanced Nitride Growth and Structures		**17:30-18:45** **Area 6:** J-5: Graphen and Oxide Devices	**17:30-18:30** **Area 9:** K-5: Novel Devices and Matarials

19:00-21:30 Rump session Room Hirose<Higashi> "Novel Lithography for more Moore/beyond CMOS and More than Moore Room Hirose<Nishi> "Solar Cells for Electronics: from In-Vehicle to Ubiquitous"

Friday, October 9

2F Heisei <Naka>	2F Heisei <Nishi>	3F Sakura	3F Keyaki	4 F Hirose <Higashi>	4F Hirose <Nishi>	6F Kiri	6F Kaede	6F Hagi	6F Aoi
9:00-10:20 **Area 1:** B-6: Epitaxy	**9:00-10:20** **Area 3:** C-6: High-k/Metal-Gate	**9:00-10:30** **Area 5:** D-6: Image Sensing Devices	**9:00-10:30** **Area 13:** E-6: Semiconductor Nanowires (I)	**9:00-10:30** **Area 10:** F-6: Organic Transistor	**9:00-10:40** **Area 4:** G-6: FeRAM/MRAM	**9:00-10:30** **Area 14:** H-6: Power Devices and Applications	**9:00-10:30** **Area 7:** I-6: Quantum Dot Devices	**9:00-10:15** **Area 11:** J-6: NEMS and MEMS	**9:00-10:30** **Area 12:** K-6: Spintronics (I): Spintronic Materials & Devices
10:35-12:15 **Area 1:** B-7: Ge-MOS	**10:45-12:15** **Area 1&3: Joint Session** C-7: FinFETs and Multi-Gate FETs	**10:45-12:05** **Area 5:** D-7: Physical Subjects for Low-power Circuit/ Device Design	**10:45-12:15** **Area 13:** E-7: Si Nanowires	**10:45-12:00** **Area 10:** F-7: Organic Electronics & Transistor	**10:45-12:15** **Area 4:** G-7: ReRAM	**10:45-12:15** **Area 14:** H-7: Materials for Power Devices	**10:45-12:15** **Area 7:** I-7: Photo Diodes	**10:45-12:15** **Area 11:** J-7: Bio Seosors and Bio Chips	**10:45-12:15** **Area 12:** K-7: Spintronics (II): Magnetic Tunnel Junction
13:15-15:05 **Area 1:** B-8: Doping Technology	**13:15-14:35** **Area 3:** C-8: Transport Physics	**13:15-15:05** **Area 2:** D-8: Advanced Material/ Process Technology	**13:15-15:15** **Area 13:** E-8: Carbon Nanotubess and Graphene	**13:15-15:15** **Area 10:** F-8: Organic Electronics & Photonics	**13:15-15:15** **Area 6:** G-8: GaN Processing and Interface Technologies	**13:15-15:00** **Area 14:** H-8: New Approaches to High-efficiency Solor Cells	**13:15-15:15** **Area 7:** I-8: LED II	**13:15-15:15** **Area 11:** J-8: Nanotechnology for Bio Sensing	**13:15-15:15** **Area 12:** K-8: Spintronics (III): Special Session on Spin-related Phenomena and Future Devices
15:20-17:10 **Area 1&3: Joint Session** B-9: Device Reliability		**15:15-17:05** **Area 2:** D-9: Characterization and Reliability for Low-k Materials	**15:30-17:15** **Area 13:** E-9: Semiconductor Nanowires (II)	**15:30-16:45** **Area 10:** F-9: Organic Transistor & Light Emitting Diode	**15:30-17:15** **Area 9:** G-9: Physics and Applications of Graphene	**15:30-17:00** **Area 14:** H-9: Materials Science for Solor Cells	**15:30-16:45** **Area 7:** I-9: Nonliner Optical Devices	**15:30-17:00** **Area 11:** J-9: Bio Nano Process	**15:30-16:45** **Area 12:** K-9: Spintronics (IV): Special Session on Spin-related Phenomena and Future Devices

Area Scope

Area 1: Advanced Gate Stack / Si Processing & Material Science
Area 2: Characterization and Materials Engineering for Interconnect Integration
Area 3: CMOS Devices /Device Physics
Area 4: Advanced Memory Technology
Area 5: Advanced Circuits and Systems
Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics
Area 7: Photonic Devices and Device Physics
Area 8: Advanced Material Synthesis and Crystal Growth Technology
Area 9: Physics and Applications of Novel Functional Materials and Devices
Area 10: Organic Materials Science, Device Physics, and Applications
Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices)
Area 12: Spintronic Materials and Devices
Area 13: Applications of Nanotubes and Nanowires
Area 14: Power Electronics